IFX4/1722

PATENT APPLICATION

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re-application of

Docket No: Q77954

Fumio MATSUMOTO

Appln. No.: 10/575,081

Group Art Unit: 1722

Confirmation No.: 8636

Examiner: Not Yet Assigned

Filed: November 28, 2006

For: COMPOUND SEMICONDUCTOR SINGLE CRYSTAL AND PRODUCTION

PROCESS THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

INFORMATION DISCLOSURE STATEMEN'T

U.S. Appln. No.: 10/575,081

Attorney Docket No.: Q77954

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant encloses herewith a copy of a Communication from a foreign patent office in a counterpart application citing such documents (German Office Action for German Patent Application No. 11 2004 001 866.8 dated July 10, 2007), together with an English-language version (if not already included) of at least that portion of the Communication indicating the degree of relevance found by the foreign patent office.

Additionally, in compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that U.S. Patent Application Publication No. US 2007/0079751 A1 corresponds to DE 11 2004 001 269.

JP 3-40987 was previously submitted in the Information Disclosure Statement filed April 7, 2006.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

Abraham J. Rosner

Registration No. 33,276

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 $\begin{array}{c} \text{WASHINGTON OFFICE} \\ 23373 \end{array}$

CUSTOMER NUMBER

Date: August 20, 2007

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STATEMENT UNDER 37 C.F.R. § 1.97(e)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The undersigned hereby states, upon information and belief:

That each item of information contained in the Information Disclosure Statement filed concurrently herewith was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of said Information Disclosure Statement.

Respectfully submitted,

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Substitute for Form 1449 A & B/PTO				Complete if Known			
				A	pplication Number	10/575,081	
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						rst Named Inventor	Fumio MATSUMOTO
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Sheet 1 of 1						torney Docket Number	Q77954

U.S. PATENT DOCUMENTS							
Examiner Cite No. 1	Cita	Document N	umber	Publication Date			
		Number	Number Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document		
		US 2007/0079751	Al	04-12-2007	MATSUMOTO		
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• *	FOREIGN PATENT DOCUMENTS							
Examiner Cite Initials* No.1	Cite	Foreign Patent Document			Publication Date	Name of Patentee or		
	Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶		
		DE	11 2004 001 269	Т5	07-20-2006	SHOWA DENKO KK	Abstract (of corresponding US 2007/0079751 A1)	
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶		
		Yasumasa OKADA, et al.; "Mechanism of a Reduction of Dislocation Densities in Vertical-Gradient-Freeze-Grown GaAs Single Crystals"; Japanese Journal of Applied Physics; Vol. 29; No. 11; November 1990; pp. L 1954-L 1956			
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Examiner Signature	l	Date Considered	
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^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.